

PD57030 PD57030S

RF POWER TRANSISTORS The LdmoST Plastic FAMILY

TARGET DATA

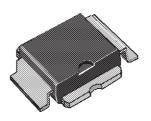
N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- POUT = 30 W with 13 dB gain @ 945 MHz / 28V
- NEW RF PLASTIC PACKAGE

DESCRIPTION

The PD57030 is a common source N-Channel, enhancement-mode, lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 28V in common source mode at frequencies of up to 1GHz. PD57030 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF. PD57030's superior linearity performance makes it an ideal solution for base station applications.

The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.



PowerSO-10RF (Formed Lead) ORDER CODE BRANDING PD57030 XPD57030



PowerSO-10RF (Straight Lead) ORDER CODE BRANDING PD57030S XPD57030S

ABSOLUTE MAXIMUM RATINGS (TCASE = 25 °C)

Symbol	Parameter	Value	Unit		
V _{(BR)DSS}	Drain-Source Voltage	e Voltage 65			
V _{GS}	Gate-Source Voltage	±20	V		
I _D	Drain Current 4		А		
P _{DISS}	Power Dissipation (@ Tc = 70° C) 52.8		W		
Tj	Max. Operating Junction Temperature 165		0C		
T _{STG}	Storage Temperature	-65 to 175	°C		

THERMAL DATA ($T_{CASE} = 70 \, {}^{\circ}C$)

R _{th(j-c)}	Junction-Case Thermal Resistance	1.8	0C/W
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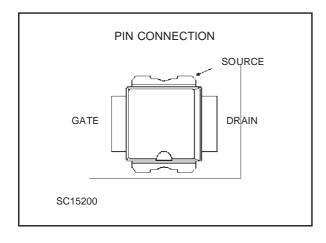
ELECTRICAL SPECIFICATION(T_{CASE} = 25 °C)

STATIC

Symbol	Parameter			Min.	Тур.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	$I_{DS} = 10mA$		65			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 28V				1	μА
I _{GSS}	V _{GS} = 20V	$V_{DS} = 0V$				1	μА
V _{GS(Q)}	V _{DS} = 28V	$I_D = 50 \text{mA}$		2.0		5.0	V
V _{DS(ON)}	V _{GS} = 10V	$I_D = 3A$			1.3		V
9FS	$V_{DS} = 10V$	$I_D = 3A$			1.8		mho
Ciss	Vgs = 0 V	V _{DS} = 28V	f = 1 MHz		57		pF
Coss	V _{GS} = 0 V	$V_{DS} = 28V$	f = 1 MHz		30		pF
C _{RSS}	$V_{GS} = 0 V$	$V_{DS} = 28V$	f = 1 MHz		1.4		pF

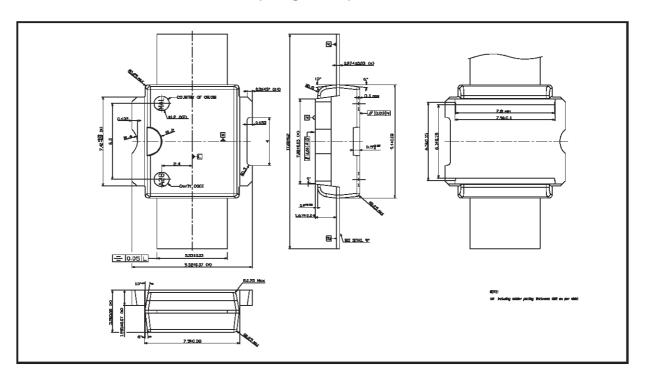
DYNAMIC

Symbol	Parameter				Min.	Тур.	Max.	Unit
Роит	$V_{DD} = 28V$	f = 945 MHz	$I_{DQ} = 50mA$		30			W
GPS	$V_{DD} = 28V$	f = 945 MHz	Pout = 30W	$I_{DQ} = 50 \text{mA}$	13	14		dB
ηD	$V_{DD} = 28V$	f = 945 MHz	P _{OUT} = 30W	$I_{DQ} = 50 \text{mA}$	50	60		%
LOAD Mismatch	V _{DD} = 28V ALL PHASE	f = 945MHz ANGLES	P _{OUT} = 30W	$I_{DQ} = 50 \text{mA}$	10:1			VSWR

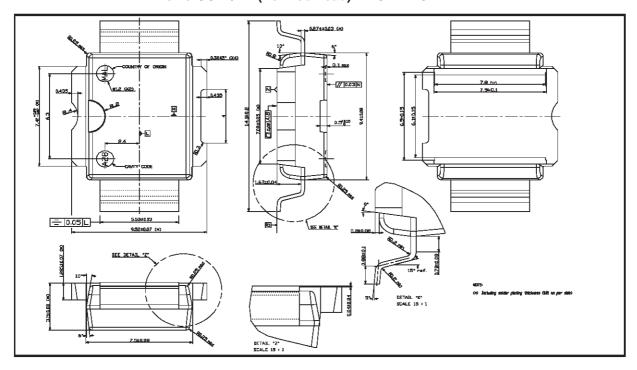


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PowerSO-10RF (Straight Lead) MECHANICAL DATA



PowerSO-10RF (Formed Lead) MECHANICAL DATA



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